## NSN 5962-01-273-8055

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nanoseconds propagation delay time, high to low level

View Online at https://aerobasegroup.com/nsn/5962-01-273-8055

Body L	ength:
0.840 ir	iches
Body V	/idth:
Betwee	n 0.220 inches and 0.310 inches
Body H	eight:
0.185 ir	iches
Maxim	Im Power Dissipation Rating:
739.0 n	illiwatts
Operat	ng Tempurature Range:
-55.0/+	125.0 degrees celsius
Storage	e Tempurature Range:
-65.0/+	150.0 degrees celsius
Feature	es Provided:
Schottk	y and programmable and bipolar and 3-state output and high impedance
Inclosu	re Material:
Cerami	
Inclosu	re Configuration:
Dual-in-	line
Output	Logic Form:
Transis	tor-transistor logic
Input C	ircuit Pattern:
10 inpu	t
Case O	utline Source And Designator:
D-2 mil	m-38510
Termin	al Surface Treatment:
Solder	
Voltage	Rating And Type Per Characteristic:
7.0 volt	s power source
Time R	ating Per Chacteristic:
75.00 n	anoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay tim
output	
Memor	y Device Type:
Rom	
Test Da	ita Document:
96906-1	nil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Termin	al Type And Quantity:
16 print	ed circuit
Shelf L	ife:
N/a	
Unit Of	Measure:
Demilit	arization:

Yes - demil/mli

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**Fiig:** A458a0

